



**ZVN3320F** 

#### SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max
200V	25Ω @ V <sub>GS</sub> = 10V	60mA

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Battery-operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

# **Features and Benefits**

- Low Input Capacitance
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

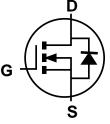
#### **Mechanical Data**

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

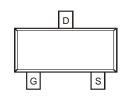
SOT23



Top View



Internal Schematic



Top View Pinout

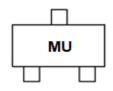
#### **Ordering Information** (Note 4)

Part Number	Pookogo	Pa	cking
Part Number	Раскаде	Qty.	Carrier
ZVN3320FTA	SOT23	3000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



MU = Product Type Marking Code



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	200	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current	ID	60	mA
Maximum Body Diode Forward Current	Is	60	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	1	Α
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	Ism	1	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	330	mW
Thermal Resistance, Junction to Ambient (Note 5)	Reja	380	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

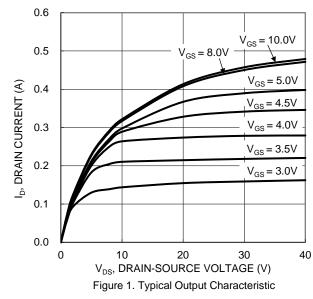
# **Electrical Characteristics** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)				•	•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	200	_	_	V	VGS = 0V, ID = 1mA
Zero Gate Voltage Drain Current	IDSS		_	10 50	μА	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V, T <sub>A</sub> = +125°C
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
On-State Drain Current	I <sub>D(on)</sub>	250	_	_	mA	V <sub>G</sub> S = 10V, V <sub>D</sub> S = 25V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	17	25	Ω	V <sub>G</sub> S = 10V, I <sub>D</sub> = 100mA
Forward Transconductance	<b>g</b> fs	75	_	_	mS	V <sub>DS</sub> = 25V, I <sub>D</sub> = 100mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	_	45		251/1/ 21/
Output Capacitance	Coss	_	_	18	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	5		
Turn-On Delay Time (Note 8)	t <sub>D(ON)</sub>	_	_	5		
Turn-On Rise Time (Note 8)	t <sub>R</sub>	_	_	7	1	V <sub>DS</sub> = 25V, I <sub>D</sub> = 100mA
Turn-Off Delay Time (Note 8)	t <sub>D(OFF)</sub>	_	_	6	ns	
Turn-Off Fall Time (Note 8)	t <sub>F</sub>	_	_	6		

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to product testing.
- 8. Switching times measured with  $50\Omega$  source impedance and <5ns rise time on a pulse generator.





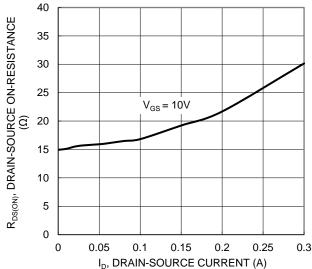


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

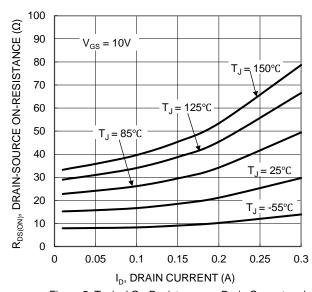


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

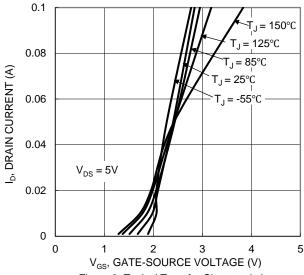


Figure 2. Typical Transfer Characteristic

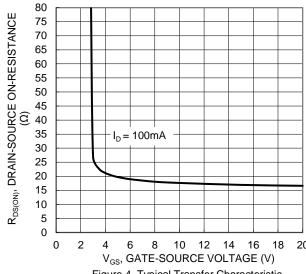


Figure 4. Typical Transfer Characteristic

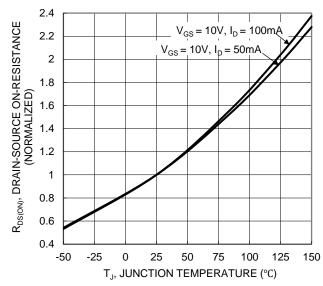
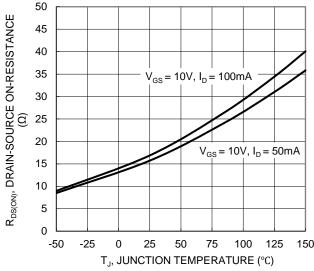
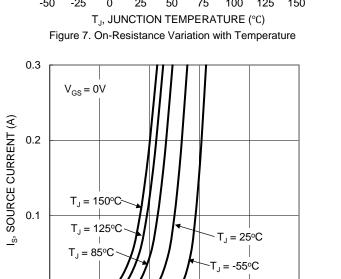


Figure 6. On-Resistance Variation with Temperature







V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

0.9

1.2

1.5

0.6

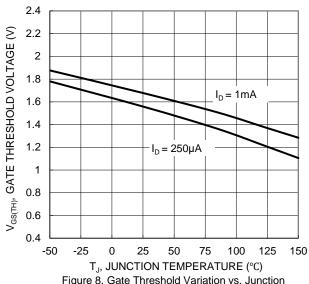


Figure 8. Gate Threshold Variation vs. Junction Temperature

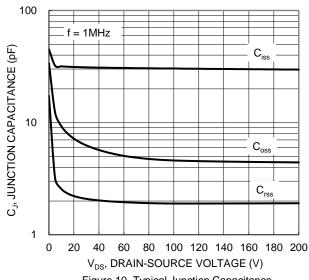


Figure 10. Typical Junction Capacitance

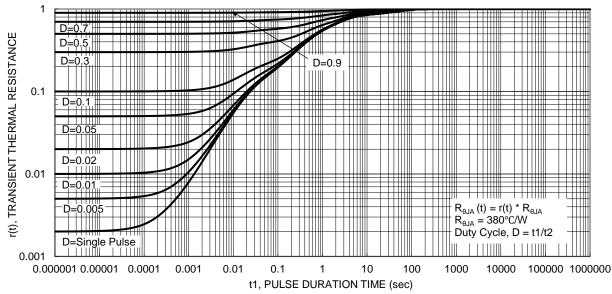


Figure 11. Transient Thermal Resistance

0

0

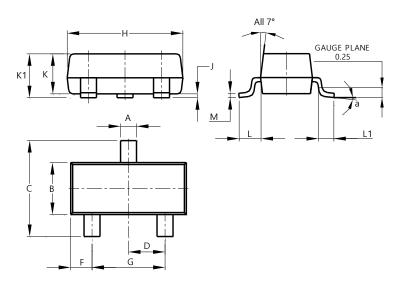
0.3



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

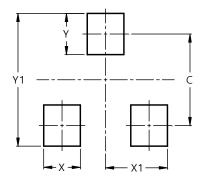


SOT23				
Dim	Min	Max	Тур	
Α	0.37	0.51	0.40	
В	1.20	1.40	1.30	
C	2.30	2.50	2.40	
D	0.89	1.03	0.915	
F	0.45	0.60	0.535	
G	1.78	2.05	1.83	
H	2.80	3.00	2.90	
7	0.013	0.10	0.05	
K	0.890	1.00	0.975	
<b>K</b> 1	0.903	1.10	1.025	
L	0.45	0.61	0.55	
L1	0.25	0.55	0.40	
М	0.085	0.150	0.110	
а	0°	8°		
All Dimensions in mm				

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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